

(61)

$$\bar{i}_1 = j\omega(C_{gs} + C_{mil}) \bar{v}_{gs}$$

$$\bar{i}_d = g_m \bar{v}_{gs}$$

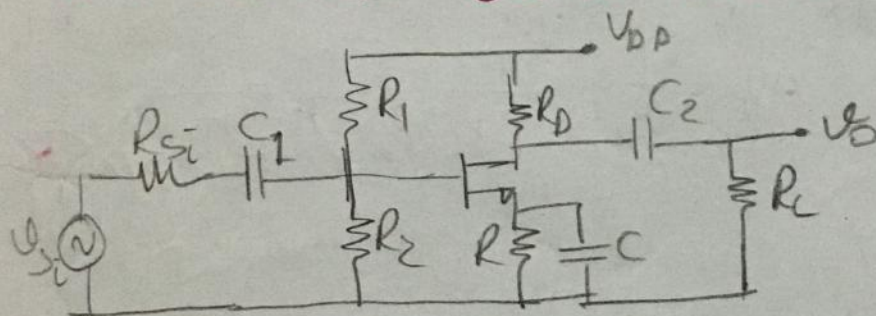
$$|A_T| = \left| \frac{\bar{i}_d}{\bar{i}_1} \right| = \frac{g_m}{2\pi f (C_{gs} + C_{mil})}$$

C_G : total input capacitance

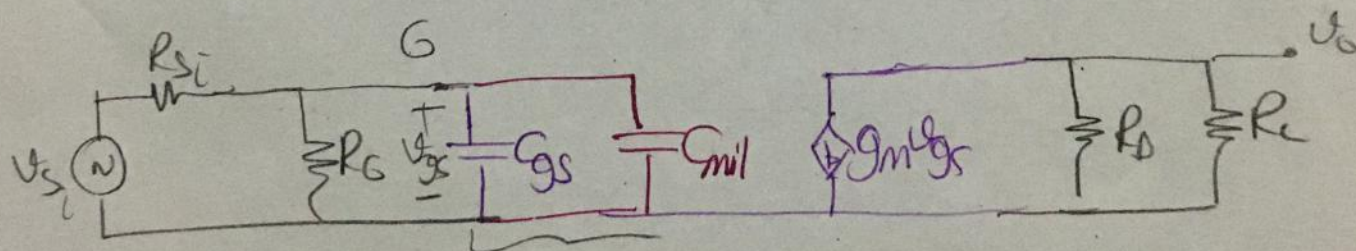
$$f_T = \frac{g_m}{2\pi (C_{gs} + C_{mil})} = \frac{g_m}{2\pi C_G}$$

5.3 High-Frequency Response of MOSFET Circuits.

5.3.1 Common Source Circuit:



high frequency equivalent circuit becomes:



$$C_G = C_{gs} + C_{mil}, \quad C_{mil} = C_{gd} \cdot (1 + g_m R_L'), \quad R_G = R_1 \parallel R_2$$

$$R_L' = R_D \parallel R_L$$

$$v_o = -g_m v_{gs} \frac{R_D \parallel R_L}{R_L'}$$

$$v_{gs} = \frac{Z_i}{Z_i + R_{si}} \cdot v_{si}, \quad Z_i = R_G \parallel C_G = \frac{R_G}{1 + s C_G R_G}$$

$$\frac{v_d(s)}{v_i(s)} = A_v(s) = -g_m R_L' \frac{Z_i}{Z_i + R_{Si}}$$

$$A_v(s) = -g_m R_L' \frac{R_G / (1 + s R_G C_G)}{\frac{R_G}{1 + s R_G C_G} + R_{Si}}$$

$$A_v(s) = -g_m R_L' \frac{R_G}{R_G + R_{Si}(1 + s R_G C_G)} = -g_m R_L' \frac{R_G}{R_G + R_{Si}} \cdot \frac{1}{1 + s \frac{R_G R_{Si} C_G}{R_G + R_{Si}}}$$

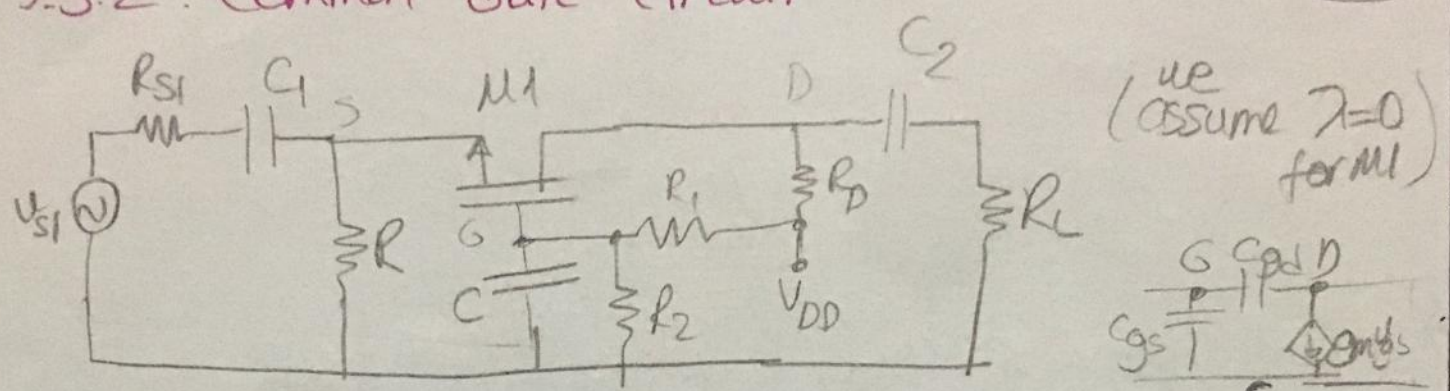
$$A_v(s) = -g_m R_L' \frac{R_G}{R_G + R_{Si}} \cdot \frac{1}{1 + s (R_G \parallel R_{Si}) C_G} \tau_H$$

$$\tau_H = C_G \cdot R_G \parallel R_{Si}, \quad \omega_H = \frac{1}{\tau_H} = \frac{1}{C_G \cdot R_G \parallel R_{Si}}, \quad f_H = \frac{1}{2\pi C_G R_G \parallel R_{Si}}$$

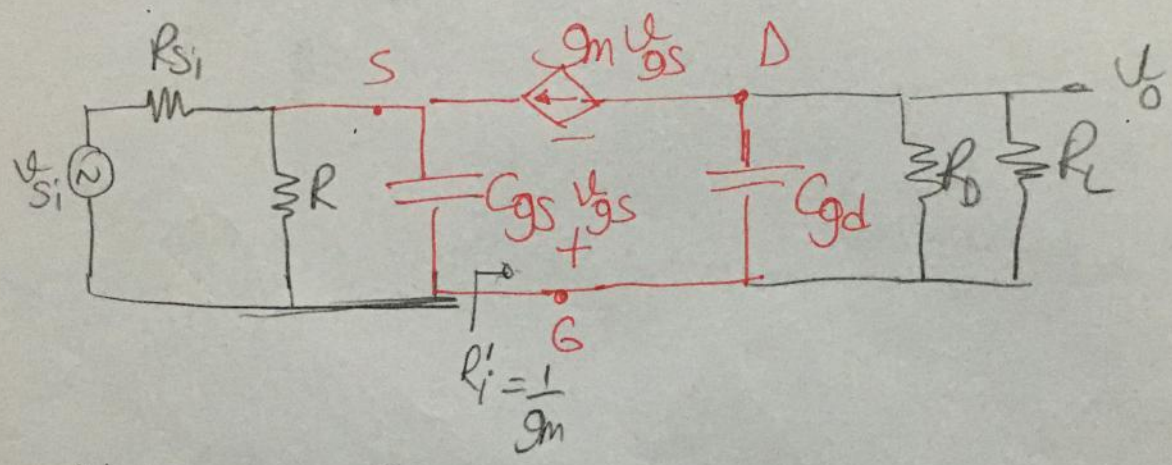
As before, we could have calculated the upper corner 3dB frequency using the time constant analysis. The effective resistance seen by the total gate capacitance C_G is $R_G \parallel R_{Si}$. Therefore

$$f_H = \frac{1}{2\pi C_G R_G \parallel R_{Si}}, \quad C_G = C_{gs} + \underbrace{C_{gd} (1 + g_m R_L')}_{C_{mil}}$$

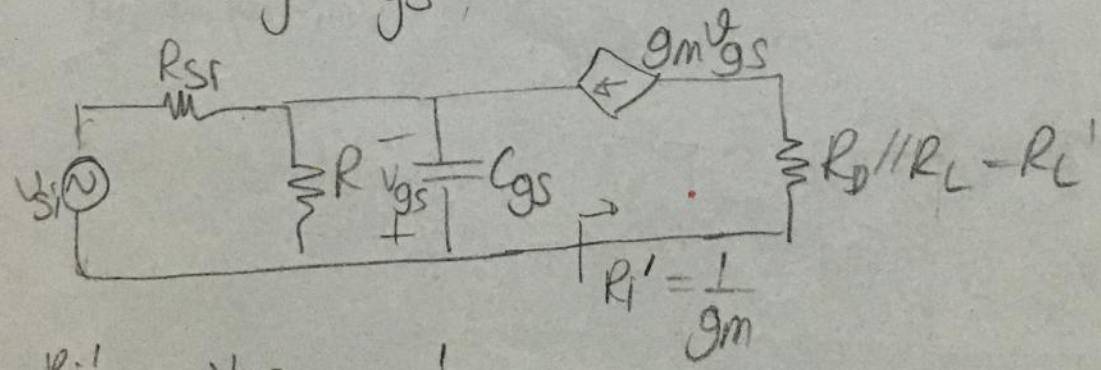
5.3.2. Common Gate Circuit



$C_1, C_2, C \rightarrow \infty$ for the high frequency analysis, s



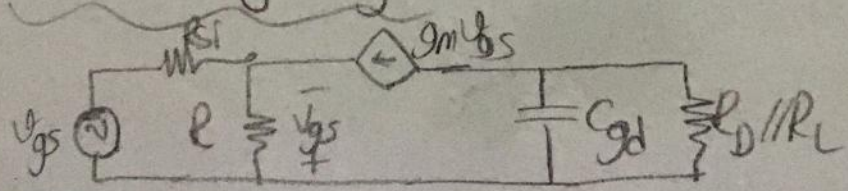
With only C_{gs}



$$R_i' = \frac{-v_{gs}}{-g_m v_{gs}} = \frac{1}{g_m}$$

$$R_{eff} C_{gs} = R_{si} || R || \frac{1}{g_m} \Rightarrow \omega_{C_{gs}} = \frac{1}{C_{gs} R_{eff} C_{gs}} = \frac{1}{C_{gs} (R_{si} || R || \frac{1}{g_m})}$$

with only C_{gd}



with $v_{si} = 0$

$$g_m v_{gs} R_{si} || R = -v_{gs}$$

$$(1 + g_m R_{si} || R) v_{gs} = 0$$

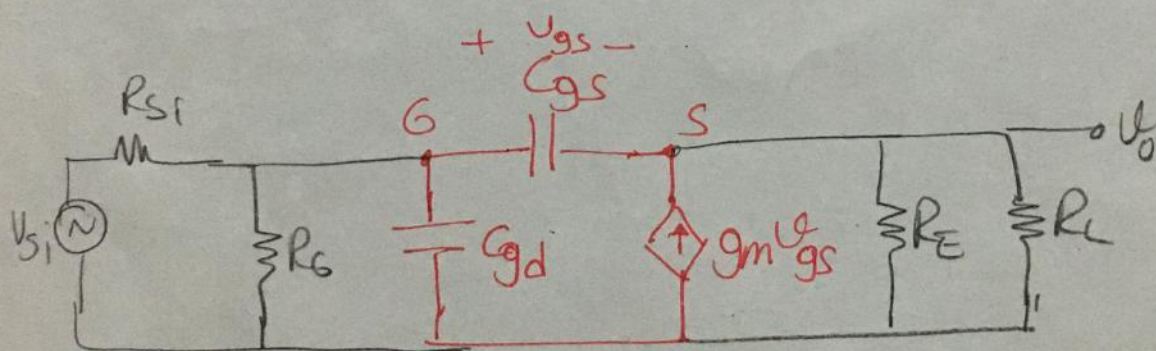
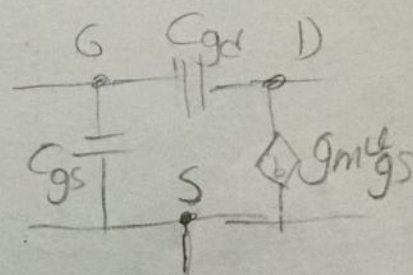
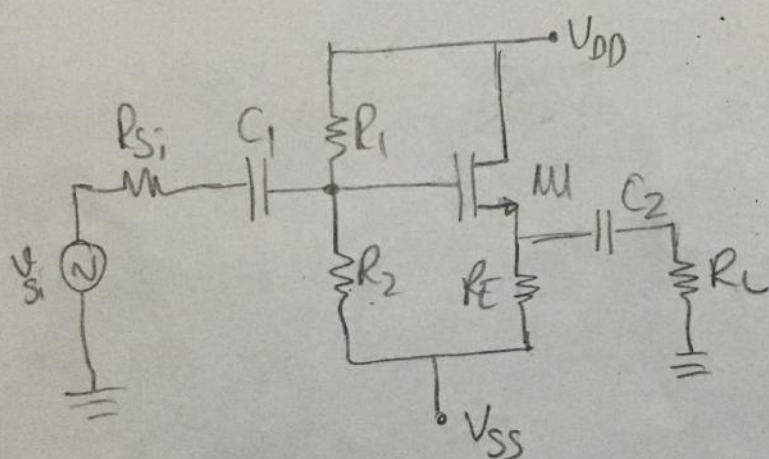
$$v_{gs} = 0$$

$$R_{effCgd} = R_L' = R_D // R_L$$

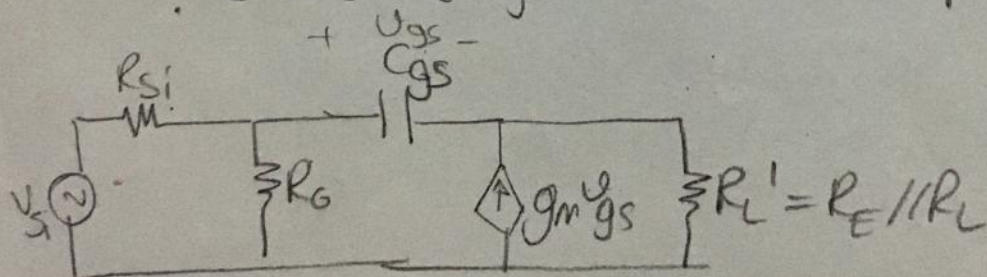
$$\omega_{Cgd} = \frac{1}{C_{gd} \cdot R_{effCgd}} = \frac{1}{C_{gd} \cdot R_D // R_L} \quad , \quad f_{Cgd} = \frac{1}{2\pi C_{gd} (R_D // R_L)}$$

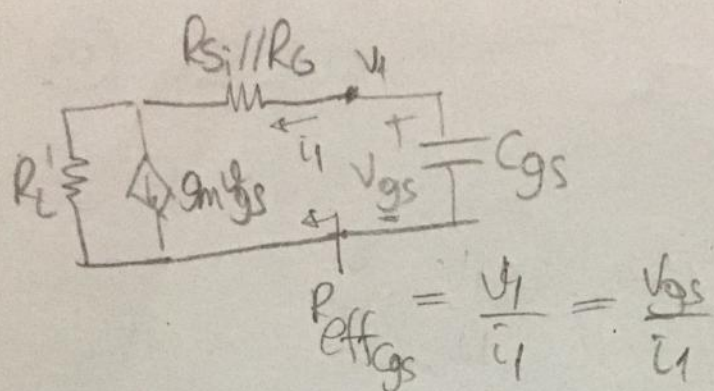
$$\omega_H = \min \{ \omega_{Cgd}, \omega_{Cgs} \} \quad , \quad f_H = \min \{ f_{Cgd}, f_{Cgs} \}$$

5.3.3 Common Drain Circuit (a.k.a. the Source Follower):



With only C_{gs} (C_{gd} is considered open circ.):





$$v_1 = R_{Si} // R_G \cdot i_1 + (i_1 - g_m v_{gs}) \cdot R_L' = v_{gs}$$

$$(R_{Si} // R_G + R_L') i_1 = (1 + g_m R_L') v_{gs}$$

$$R_{eff,gs} = \frac{v_{gs}}{i_1} = \frac{R_{Si} // R_G + R_L'}{1 + g_m R_L'}$$

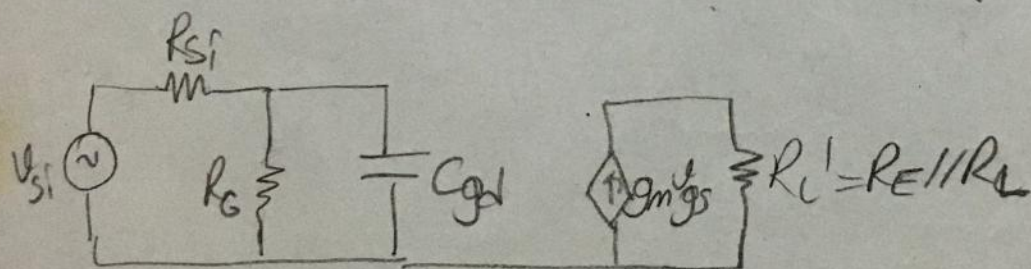
$$\omega_{Cgs} = \frac{1}{\tau_{Cgs}} = \frac{1}{C_{gs} \left[\frac{R_{Si} // R_G + R_L'}{1 + g_m R_L'} \right]}$$

$$R_L' = R_E // R_L$$

$$R_G = R_1 // R_2$$

$$f_{Cgs} = \frac{\omega_{Cgs}}{2\pi}$$

with only C_{gd} (C_{gs} is considered open circuit):



$$R_{eff,Cgd} = R_{Si} // R_G, \quad \omega_{Cgd} = \frac{1}{\tau_{Cgd}} = \frac{1}{C_{gd} \cdot R_{Si} // R_G} \quad f_{Cgd} = \frac{\omega_{Cgd}}{2\pi}$$

$$\omega_H = \min \{ \omega_{Cgd}, \omega_{Cgs} \}, \quad f_H = \min \{ f_{Cgd}, f_{Cgs} \}$$